CLAIMS

1. A sputtering target, the sputtering target containing 0.05 at% or more of Bi and having a total content of metal oxides of from 10 vol% to 60 vol%, the balance containing at least Co and Pt.

2. The sputtering target according to claim 1, wherein the sputtering target contains a part or all of Bi as a metal oxide.

3. The sputtering target according to claim 1 or 2, wherein the sputtering target contains 0.5 at% or more of Bi.

4. The sputtering target according to any of claims 1 to 3, wherein the metal oxide comprises an oxide of at least one element selected from the group consisting of Co, Cr, Si, Ti, and B.

5. The sputtering target according to any one of claims 1 to 4, wherein the sputtering target further contains from 0.5 at% to 30 at% of at least one selected from the group consisting of Au, Ag, B, Cu, Cr, Ge, Ir, Mn, Mo, Nb, Ni, Pd, Re, Rh, Ru, Ta, W, and V.

6. A magnetic film, the magnetic film containing 0.05 at% or more of Bi and having a total content of metal oxides of from 10 vol% to 60 vol%, the balance containing at least Co and Pt.

7. The magnetic film according to claim 6, wherein the magnetic film contains 0.5 at% or more of Bi.

8. The magnetic film according to claim 6 or 7, wherein the metal oxide comprises an oxide of at least one element selected from the group consisting of Co, Cr, Si, Ti, and B.

9. The magnetic film according to any one of claims 6 to 8, wherein the magnetic film further contains from 0.5 at% to 30 at% of at least one selected from the group consisting of Au, Ag, B, Cu, Cr, Ge, Ir, Mn, Mo, Nb, Ni, Pd, Re, Rh, Ru, Ta, W, and V.

10. A perpendicular magnetic recording medium comprising the granular film according to any one of claims 6 to 9.